High and Low Side Driver

Features

- Floating channel designed for bootstrap operation
- Fully operational to 200V
- Tolerant to negative transient voltage, dV/dt immune
- Gate drive supply range from 10 to 20V
- Independent low and high side channels •
- Input logic HIN/LIN active high •
- Undervoltage lockout for both channels •
- 3.3V and 5V logic compatible •
- CMOS Schmitt-triggered inputs with pull-down
- Matched propagation delay for both channels

Description

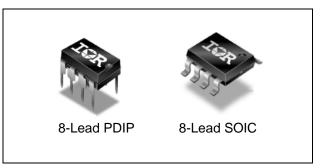
The IR2011 is a high power, high speed power MOSFET driver with independent high and low side referenced output Package Options channels. Logic inputs are compatible with standard CMOS or LSTTL output, down to 3.0V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET in the high side configuration which operates up to 200 volts. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction.

Applications

- Converters
- DC motor drive

Product Summary

V _{OFFSET} (max)	200V
I _{O+/-} (typ)	1.0A / 1.0A
V _{OUT}	10-20V
t _{on/off} (typ)	80ns & 60ns
Delay Matching (max)	20ns

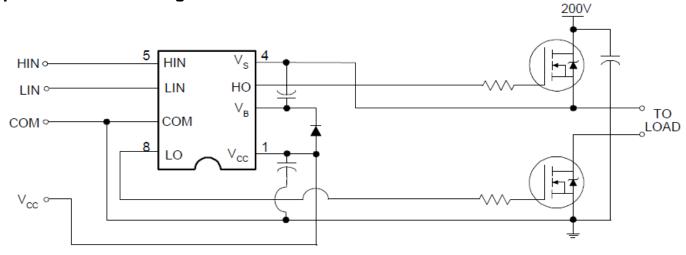


Ordering Information

Dese Dest Nevel as		Standar	d Pack	Ondenskie Deut Norsker
Base Part Number	Package Type	Form	Quantity	Orderable Part Number
IR2011PBF	PDIP8	Tube	50	IR2011PBF
IR2011SPBF	SO8N	Tube	95	IR2011SPBF
IR2011SPBF	SO8N	Tape and Reel	2500	IR2011STRPBF



Typical Connection Diagram



(Refer to Lead Assignments for correct configuration.) This diagram shows electrical connections only. Please refer to our Application Notes and Design Tips for proper circuit board layout



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V _B	High side floating supply voltage		-0.3	225	
Vs	High side floating supply offset vol	tage	V _B - 25	V _B + 0.3	
V _{HO}	High side floating output voltage		V _S - 0.3	V _B + 0.3	v
V _{cc}	Low side fixed supply voltage		-0.3	25	Ň
V _{LO}	Low side output voltage		-0.3	V _{CC} + 0.3	
V _{IN}	Logic input voltage (HIN, LIN)		-0.3	V _{CC} + 0.3	
dV _s /dt	Allowable offset supply voltage trai	nsient	—	50	V/ns
	Package power dissipation	8-Lead PDIP		1.0	14/
P _D	$P = (0, T_A \le +25^{\circ}C)$ 8-Lead SOIC	8-Lead SOIC		0.625	W
D/L	Thermal resistance, junction to	8-Lead PDIP		125	0000
Rth _{JA}	Rth _{JA} ambient			200	°C/W
TJ	Junction temperature			150	
Ts	Storage temperature	-55	150	°C	
TL	Lead temperature (soldering, 10 seconds)			300	

Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions. The V_s and COM offset ratings are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply absolute voltage	V _s + 10	V _S + 20	
Vs	High side floating supply offset voltage	+	200	
V _{HO}	High side floating output voltage	Vs	V _B	V
V _{CC}	Low side fixed supply voltage	10	20	
V _{LO}	Low side output voltage	0	V _{cc}	
V _{IN}	Logic input voltage (HIN, LIN)	COM	5.5	
T _A	Ambient temperature	-40	125	°C

+ Logic operational for V_S of -4 to +200V. Logic state held for V_S of -4V to -V_BS.



Dynamic Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V, C_L = 1000pF and T_A = 25°C unless otherwise specified. Figure 1 shows the timing definitions.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
t _{on}	Turn-on propagation delay	—	80	—		$V_{S} = 0V$
t _{off}	Turn-off propagation delay		75			V _S = 200V
t _r	Turn-on rise time	—	35	50		
t _f	Turn-off fall time	—	20	35	ns	
DM1	Turn-on delay matching t _{on} (H) - t _{on} (L)	_		20		
DM2	Turn-off delay matching t _{off} (H) - t _{off} (L)	_	_	20		

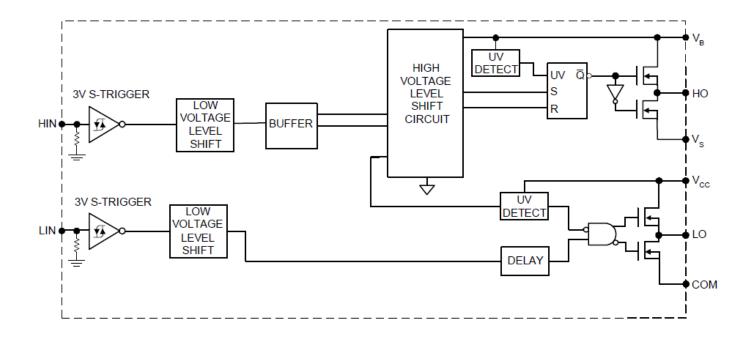
Static Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to COM and are applicable to all logic input leads: HIN and LIN. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{IH}	Logic "1" input voltage	2.2	—	—		$V_{CC} = 10V - 20V$
V _{IL}	Logic "0" input voltage			0.7	V	$v_{\rm CC} = 10v - 20v$
V _{OH}	High level output voltage, V_{BIAS} - V_{O}			2.0	v	$I_{O} = OA$
V _{OL}	Low level output voltage, V _O	_	—	0.2		$I_{O} = 20 \text{mA}$
I _{LK}	Offset supply leakage current	_	—	50		$V_{B} = V_{S} = 200V$
I _{QBS}	Quiescent V _{BS} supply current		90	210		V _{IN} = 0V or 3.3V
l _{QCC}	Quiescent V _{CC} supply current		140	230	μA	$V_{\rm IN} = 0$ V OI 3.5 V
I _{IN+}	Logic "1" input bias current		7.0	20		$V_{IN} = 3.3V$
I _{IN-}	Logic "0" input bias current			1.0		$V_{IN} = 0V$
V _{BSUV+}	V _{BS} supply undervoltage positive going threshold	8.2	9.0	9.8		
V _{BSUV-}	V _{BS} supply undervoltage negative going threshold	7.4	8.2	9.0	V	
V _{CCUV+}	V _{CC} supply undervoltage positive going threshold	8.2	9.0	9.8	v	
V _{CCUV-}	V _{CC} supply undervoltage negative going threshold	7.4	8.2	9.0		
I _{O+}	Output high short circuit pulsed current	_	1.0	_	A	V _O = 0V, PW ≤ 10 µs
I _{O-}	Output low short circuit pulsed current	_	1.0	_	A	V _O = 15V PW ≤ 10 μs



Functional Block Diagram

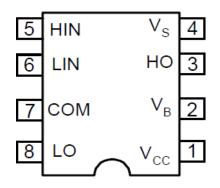


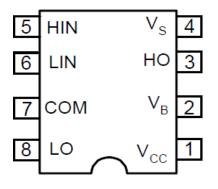


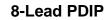
Lead Definitions

Symbol	Description
HIN	Logic input for high side gate driver outputs (HO), in phase
LIN	Logic input for low side gate driver outputs (LO), in phase
V _B	High side floating supply
HO	High side gate drive output
Vs	High side floating supply return
V _{CC}	Low side supply
LO	Low side gate drive output
COM	Low side return

Lead Assignments







8-Lead SOIC



Application Information and Additional Details

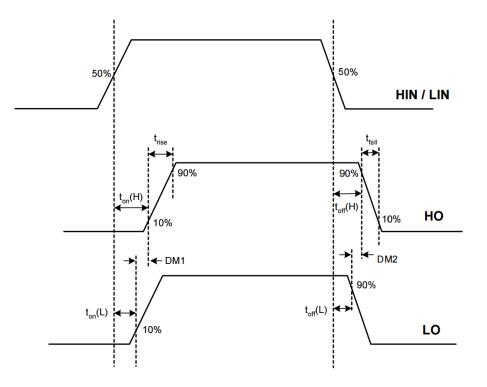
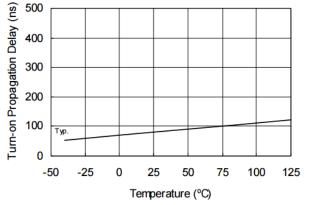
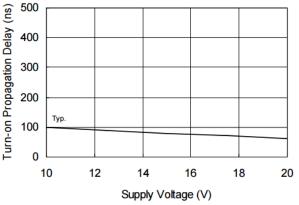


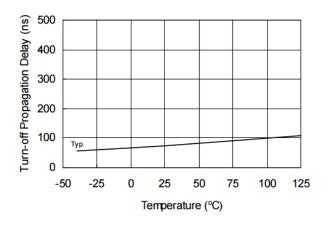
Figure 1. Timing Diagram













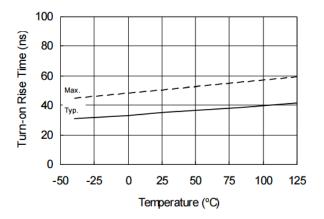


Figure 4A. Turn-on Rise Time vs. Temperature

Figure 2B. Turn-on Propagation Delay vs. Supply Voltage

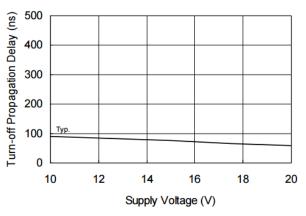


Figure 3B. Turn-off Propagation Delay vs. Supply Voltage

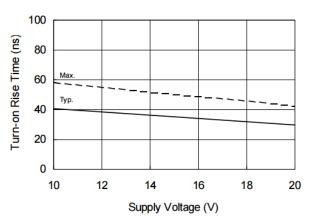
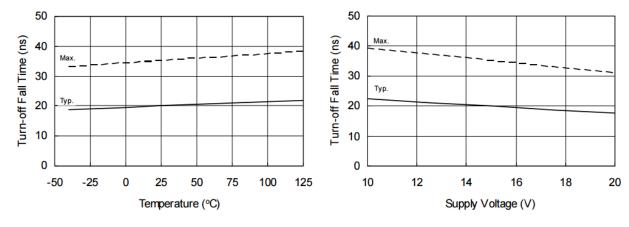
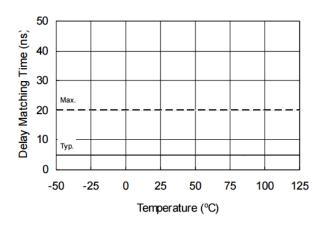


Figure 4B. Turn-on Rise Time vs. Supply Voltage











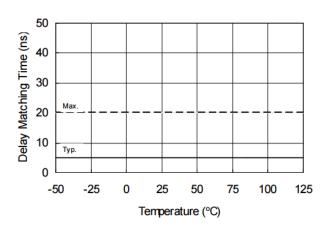




Figure 5B. Turn-off Fall Time vs. Supply Voltage

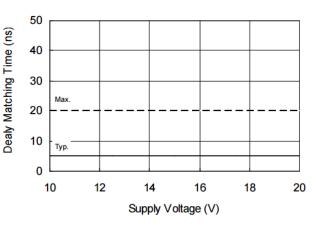


Figure 6B. Turn-on Delay Matching Time vs. Supply Voltage

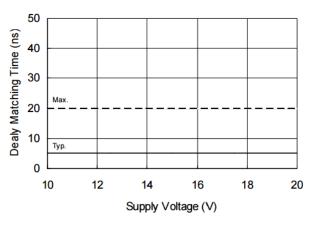
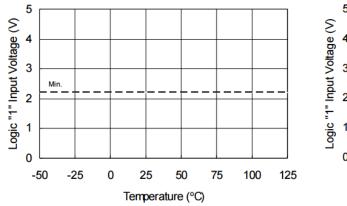


Figure 7B. Turn-off Delay Matching Time vs. Supply Voltage





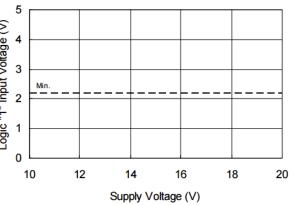


Figure 8A. Logic "1" Input Voltage vs. Temperature

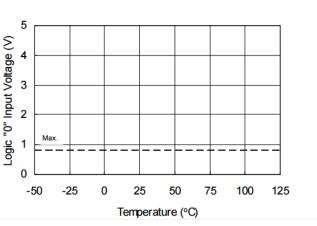


Figure 9A. Logic "0" Input Voltage vs. Temperature

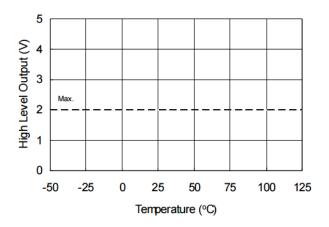


Figure 10A. High Level Output vs. Temperature

Figure 8B. Logic "1" Input Voltage vs. Supply Voltage

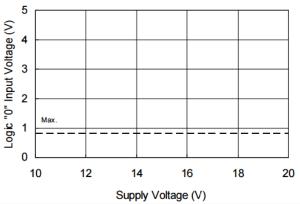
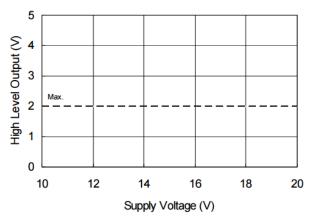
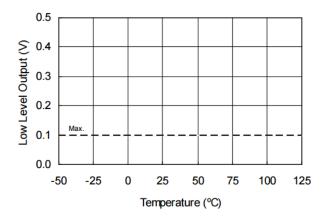


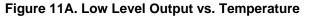
Figure 9B. Logic "0" Input Voltage vs. Supply Voltage











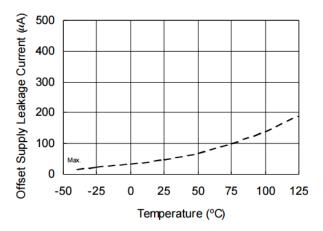


Figure 12A. Offset Supply Leakage Current vs. Temperature

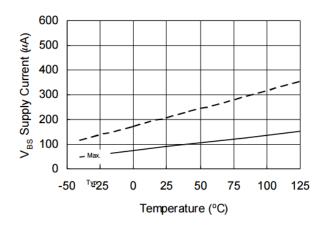


Figure 13A. V_{BS} Supply Current vs. Temperature

Low Level Output (V) 0.1 0.0 14 20 10 12 16 18 Supply Voltage (V)

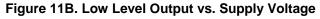
0.5

0.4

0.3

0.2

Max



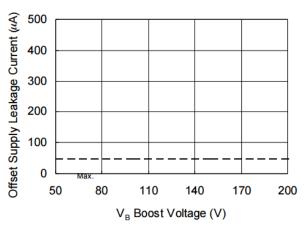


Figure 12B. Offset Supply Leakage Current vs. **Supply Voltage**

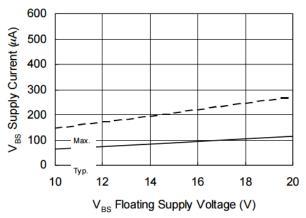
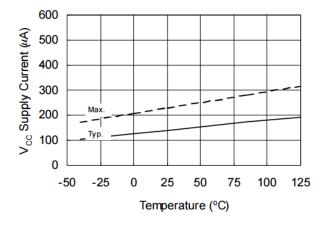


Figure 13B. V_{BS} Supply Current vs. Supply Voltage





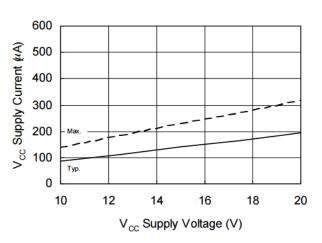


Figure 14A. V_{CC} Supply Current vs. Temperature

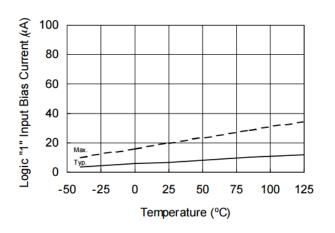


Figure 15A. Logic "1" Input Bias Current vs. Temperature

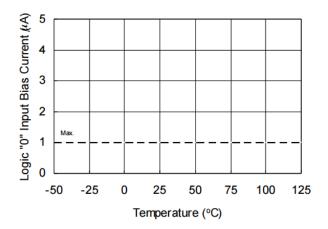


Figure 16A. Logic "0" Input Bias Current vs. Temperature

Figure 14B. V_{CC} Supply Current vs. V_{CC} Supply Voltage

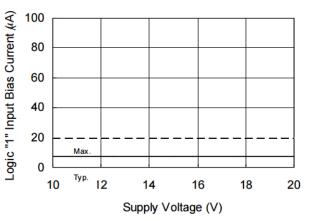


Figure 15 B. Logic "1" Input Bias Current vs. Supply Voltage

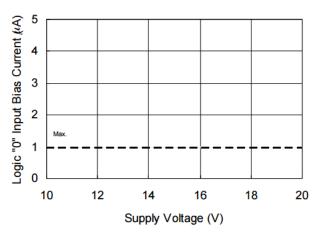
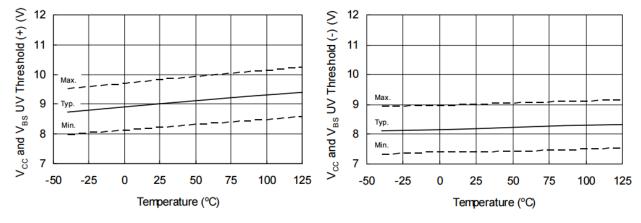
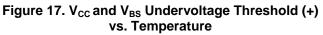


Figure 16B. Logic "0" Input Bias Current vs. Supply Voltage







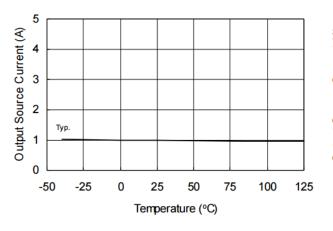


Figure 19A. Output Source Current vs. Temperature

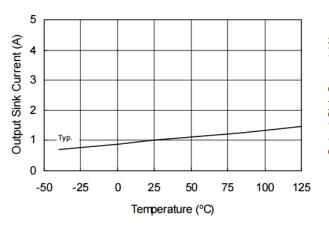


Figure 20A. Output Sink Current vs. Temperature

Figure 18. V_{CC} and V_{BS} Undervoltage Threshold (-) vs. Temperature

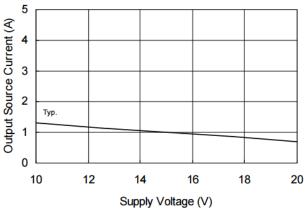


Figure 19B. Output Source Current vs. Supply Voltage

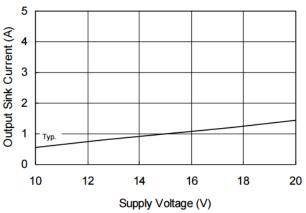
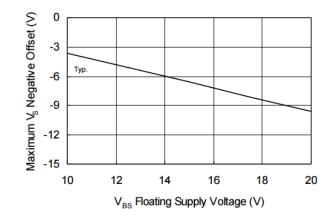
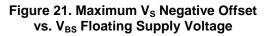


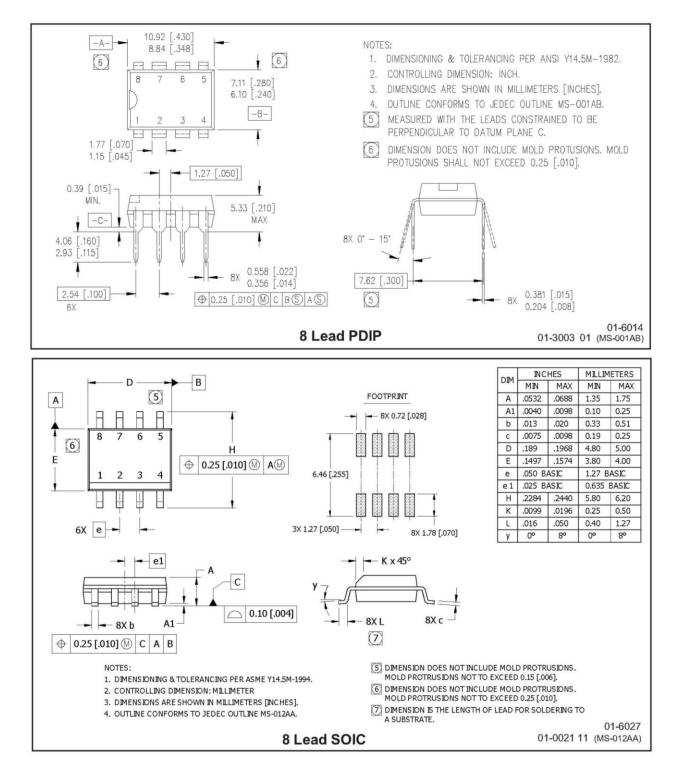
Figure 20B. Output Sink Currnt vs. Supply Voltage





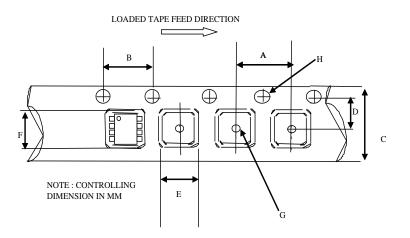


Package Details



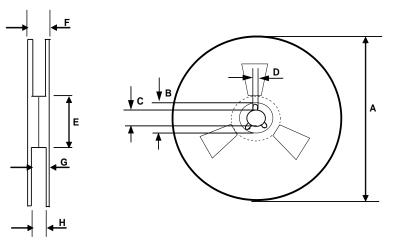


Tape and Reel Details



CARRIER TAPE DIMENSION FOR 8SOICN

	Me	tric	Imp	erial
Code	Min	Max	Min	Max
A	7.90	8.10	0.311	0.318
В	3.90	4.10	0.153	0.161
С	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
Н	1.50	1.60	0.059	0.062

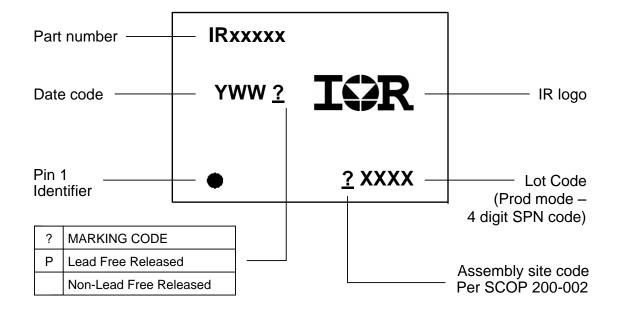


REEL DIMENSIONS FOR 8SOICN

	Me	tric	Imp	erial
Code	Min	Max	Min	Max
A	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
С	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
Н	12.40	14.40	0.488	0.566



Part Marking Information





Qualification Information[†]

Qualification Level		Industrial ^{††} (per JEDEC JESD 47)		
		Comments: This family of ICs has passed JEDEC's Industrial qualification. IR's Consumer qualification level is granted by extension of the higher Industrial level.		
Moisture Sensitivity Level 8-Lead SOIC		MSL2 ^{†††} (per IPC/JEDEC J-STD-020)		
RoHS Compliant	•	Yes		

- † Qualification standards can be found at International Rectifier's web site http://www.irf.com/
- ++ Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information.
- +++ Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.

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